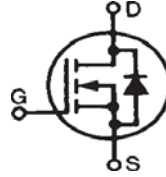


High Voltage MOSFET

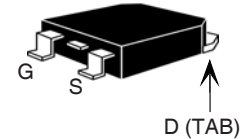
IXTH20N50D IXTT20N50D

N-Channel, Depletion Mode

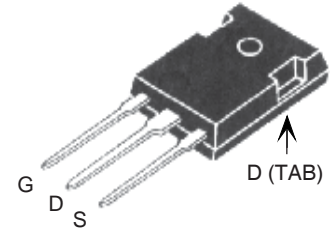
$V_{DSX} = 500V$
 $I_{D25} = 20A$
 $R_{DS(on)} \leq 330m\Omega$



TO-268 (IXTT)



TO-247 (IXTH)



G = Gate D = Drain
 S = Source TAB = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSX}	$T_J = 25^\circ C$ to $150^\circ C$	500	V
V_{DGX}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GS} = 1M\Omega$	500	V
V_{GSX}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ C$	20	A
I_{DM}	$T_C = 25^\circ C$, Pulse Width Limited by T_{JM}	50	A
P_D	$T_C = 25^\circ C$	400	W
T_J		- 55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		- 55 ... +150	$^\circ C$
T_L	1.6mm (0.062 in.) from Case for 10s	300	$^\circ C$
T_{SOLD}	Plastic Body for 10s	260	$^\circ C$
M_d	Mounting Torque (TO-247)	1.13 / 10	Nm/lb.in.
Weight	TO-268	4	g
	TO-247	6	g

Features

- Normally ON Mode
- International Standard Packages
- Molding Epoxies Meet UL 94 V-0 Flammability Classification

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- Level Shifting
- Triggers
- Solid State Relays
- Current Regulators
- Active Load

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSX}	$V_{GS} = -10V$, $I_D = 250\mu A$	500		V
$V_{GS(off)}$	$V_{DS} = 25V$, $I_D = 250\mu A$	-1.5		V
I_{GSS}	$V_{GS} = \pm 30V$, $V_{DS} = 0V$			± 100 nA
I_{DSS}	$V_{DS} = V_{DSX}$, $V_{GS} = -10V$ $T_J = 125^\circ C$			25 μA 500 μA
$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 10A$, Note 1			330 m Ω
$I_{D(on)}$	$V_{GS} = 0V$, $V_{DS} = 25V$, Note 1		2.3	A

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values			
		Min.	Typ.	Max.	
g_{fs}	$V_{DS} = 30\text{V}$, $I_D = 0.5 \cdot I_{D25}$, Note 1	4.0	6.5	9.0	S
C_{iss}	$V_{GS} = -10\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$		6300		pF
C_{oss}			385		pF
C_{rss}			82		pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = -10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSX}$, $I_D = 0.5 \cdot I_{D25}$ $R_G = 4.7\Omega$ (External)		35		ns
t_r			85		ns
$t_{d(off)}$			110		ns
t_f			75		ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSX}$, $I_D = 0.5 \cdot I_{D25}$		78.5		nC
Q_{gs}			19.2		nC
Q_{gd}			35.0		nC
R_{thJC}				0.31	$^\circ\text{C/W}$
R_{thCS}		0.21			$^\circ\text{C/W}$

Safe Operating Area Specification

Symbol	Test Conditions	Min.	Typ.	Max.
SOA	$V_{DS} = 400\text{V}$, $I_D = 0.6\text{A}$, $T_C = 75^\circ\text{C}$, $t_p = 3\text{s}$	240		W

Source-Drain Diode

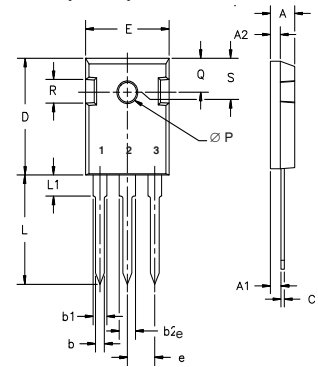
Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values			
		Min.	Typ.	Max.	
V_{SD}	$I_F = I_{D25}$, $V_{GS} = -10\text{V}$, Note 1		0.75	1.4	V
t_{rr}	$I_F = 20\text{A}$, $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$, $V_{GS} = -10\text{V}$		590		ns
I_{RM}			32.6		A
Q_{RM}			9.6		μC

Note 1: Pulse Test, $t \leq 300\mu\text{s}$; Duty Cycle, $d \leq 2\%$.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

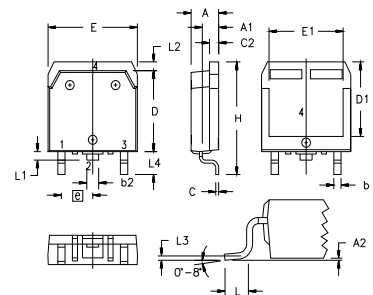
TO-247 (IXTH) Outline



Terminals: 1 - Gate
2 - Drain
3 - Source
Tab - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	242	BSC

TO-268 (IXTT) Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

Fig. 1. Output Characteristics @ 25°C

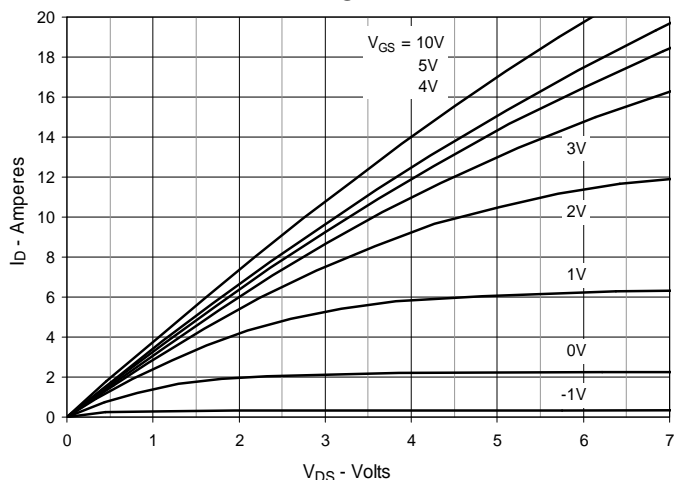


Fig. 2. Extended Output Characteristics @ 25°C

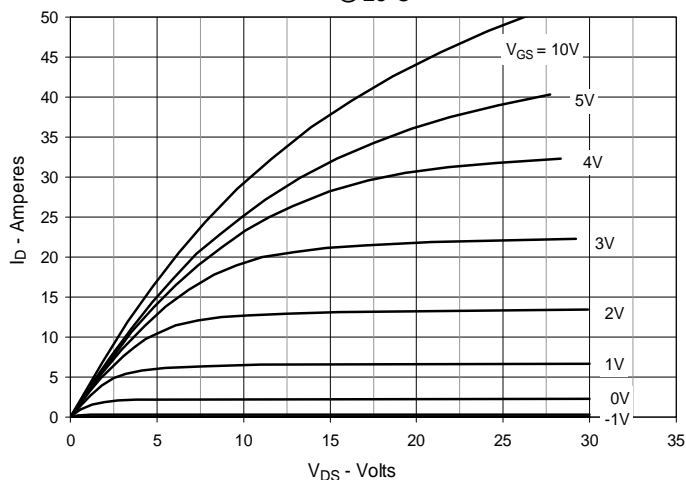


Fig. 3. Output Characteristics @ 125°C

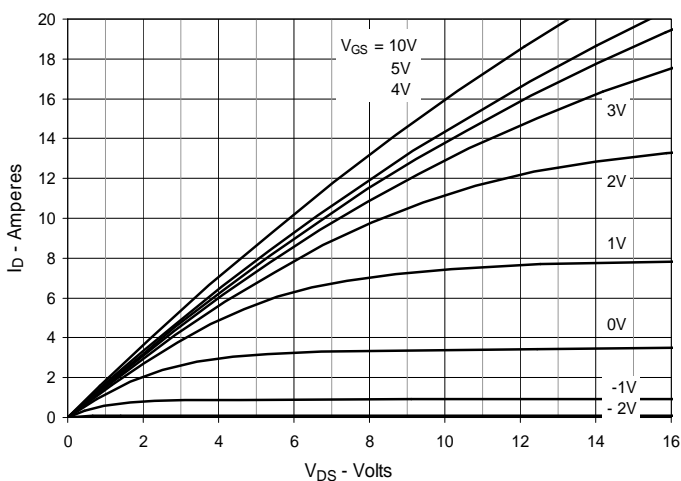


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 10A$ Value vs. Junction Temperature

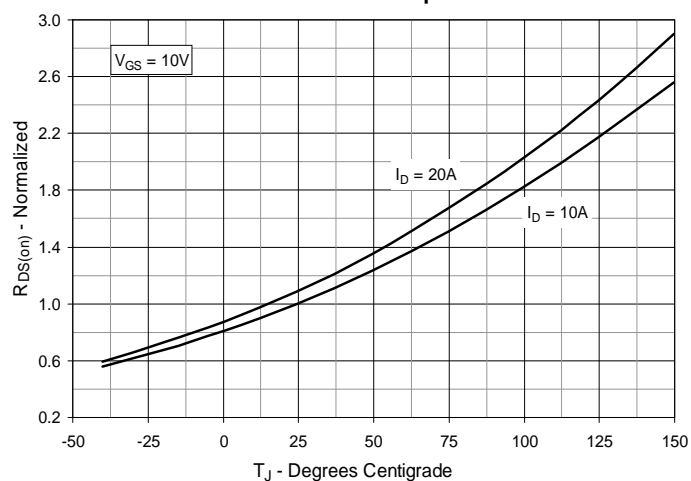


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 10A$ Value vs. Drain Current

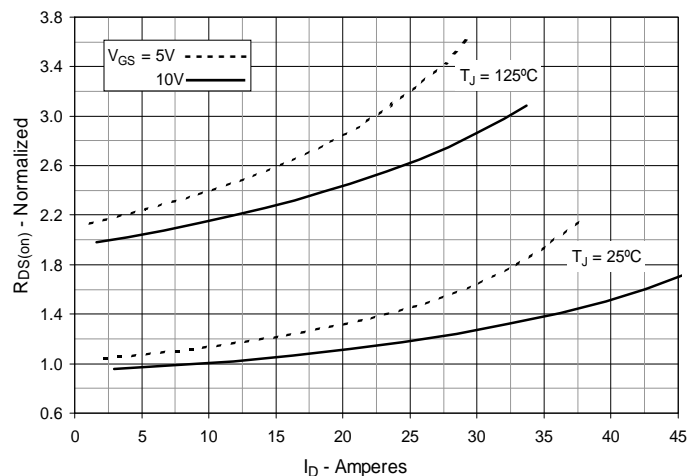


Fig. 6. Maximum Drain Current vs. Case Temperature

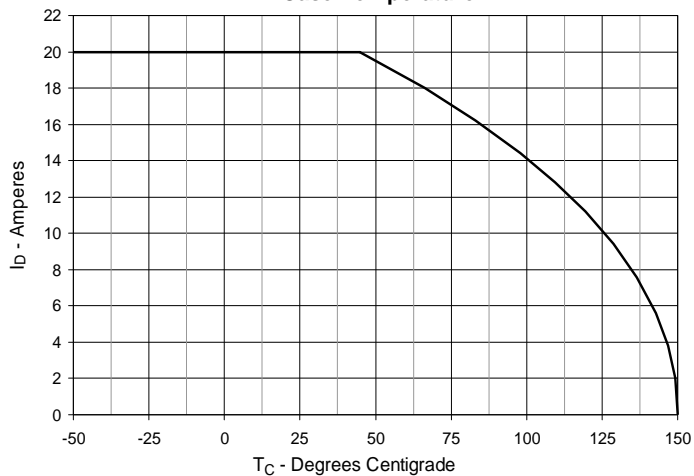


Fig. 7. Input Admittance

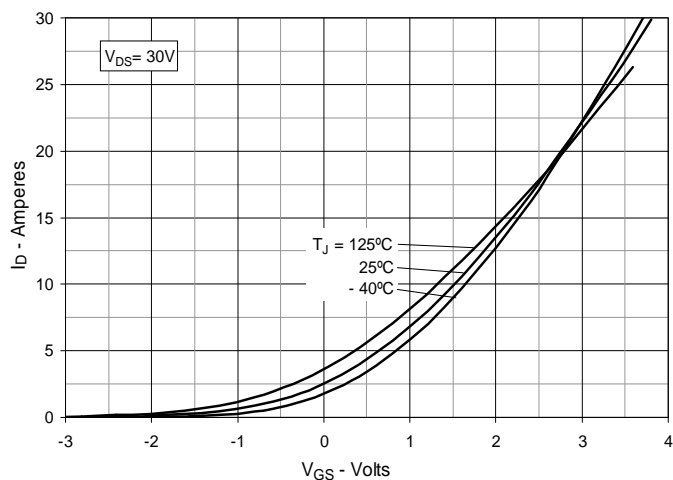


Fig. 8. Transconductance

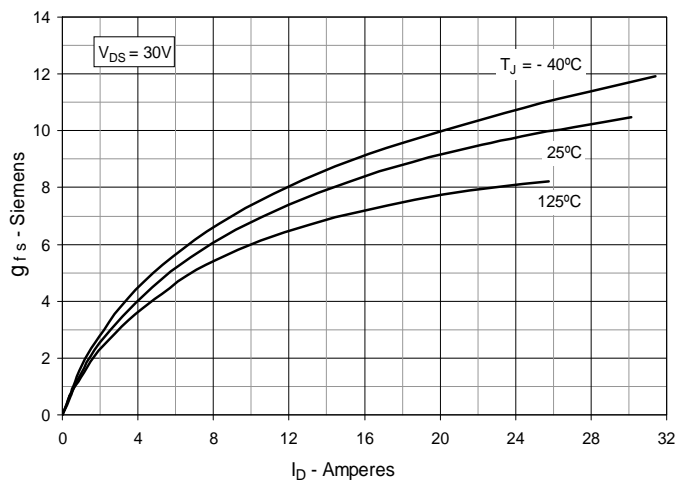


Fig. 9. Forward Voltage Drop of Intrinsic Diode

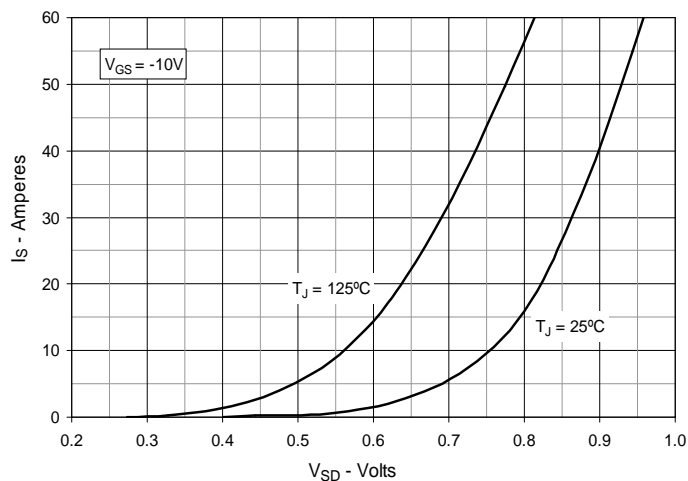


Fig. 10. Breakdown and Threshold Voltages vs. Junction Temperature

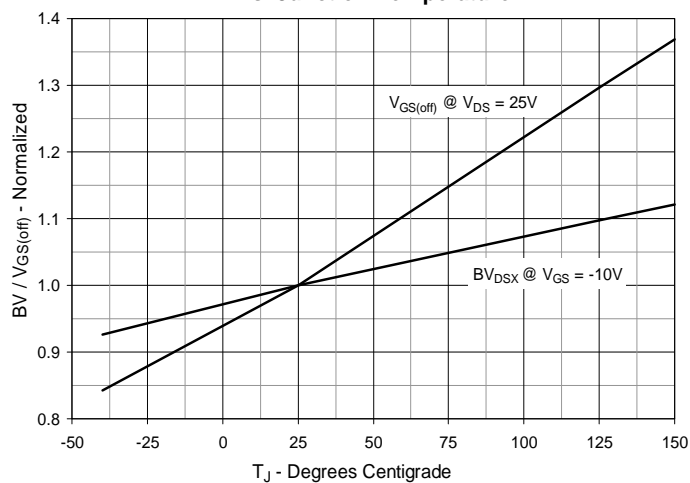


Fig. 11. Gate Charge

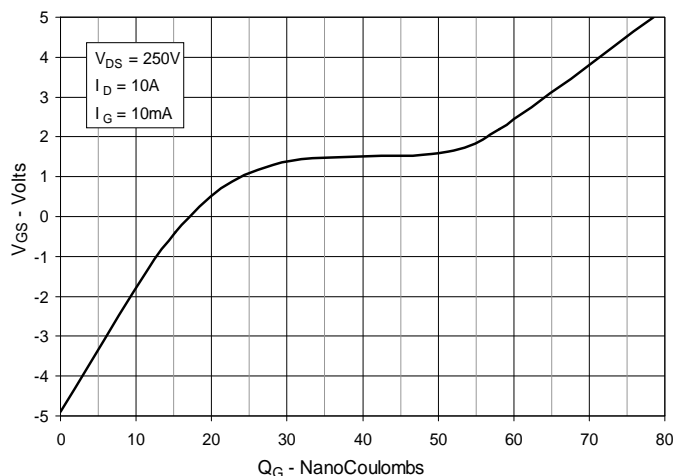


Fig. 12. Capacitance

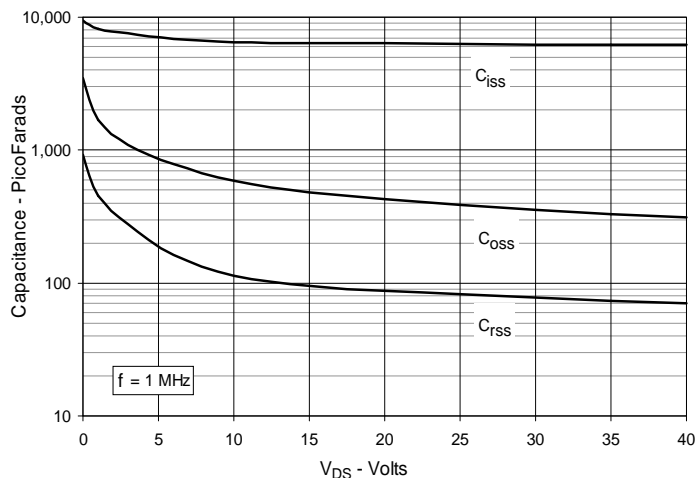


Fig. 13. Forward-Bias Safe Operating Area
@ $T_C = 25^\circ\text{C}$

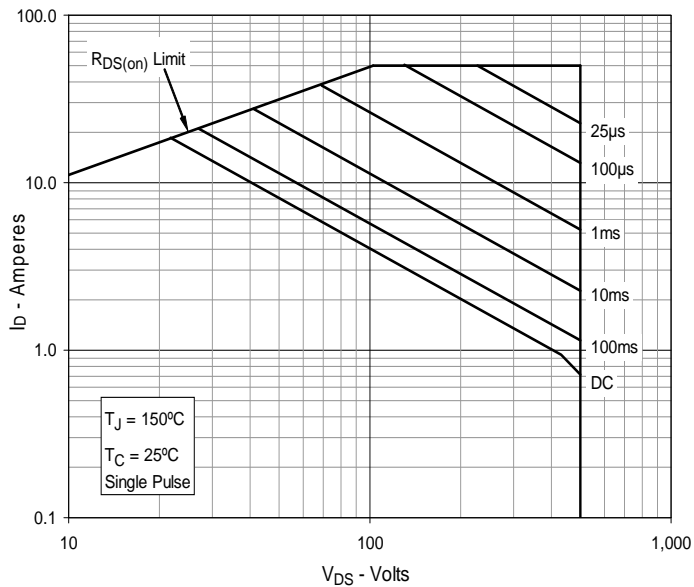


Fig. 14. Forward-Bias Safe Operating Area
@ $T_C = 75^\circ\text{C}$

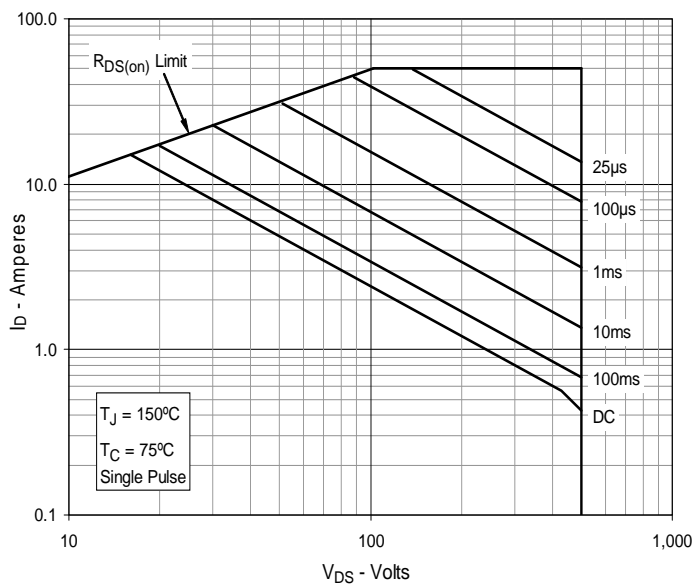


Fig. 15. Maximum Transient Thermal Impedance

